

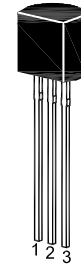
2SC2668

NPN Silicon Epitaxial Planar Transistor

High frequency amplifier applications.

The transistor is subdivided into three groups, R, O and Y, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	I_C	20	mA
Base Current	I_B	4	mA
Power Dissipation	P_{tot}	100	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at V _{CE} = 6 V, I _C = 1 mA	Current Gain Group R O Y	h _{FE}	40	-	80	-
		h _{FE}	70	-	140	-
		h _{FE}	100	-	200	-
Collector Base Cutoff Current at V _{CB} = 40 V	I _{CBO}	-	-	500	nA	
Emitter Base Cutoff Current at V _{EB} = 4 V	I _{EBO}	-	-	500	nA	
Transition Frequency at V _{CE} = 6 V, I _C = 1 mA	f _T	-	550	-	MHz	
Reverse Transfer Capacitance at V _{CE} = 6 V, f = 1 MHz	C _{re}	-	0.7	-	pF	

